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6 A, 600 V hyper fast IGBT

## Features

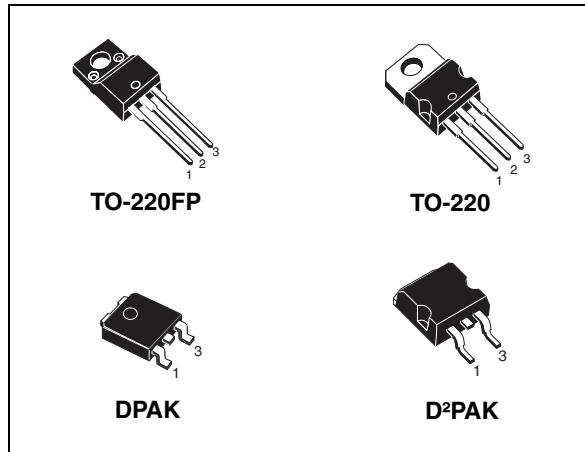
- Low  $C_{RES}$  /  $C_{IES}$  ratio (no cross-conduction susceptibility)
- Very high frequency operation
- Very soft ultrafast recovery antiparallel diode

## Applications

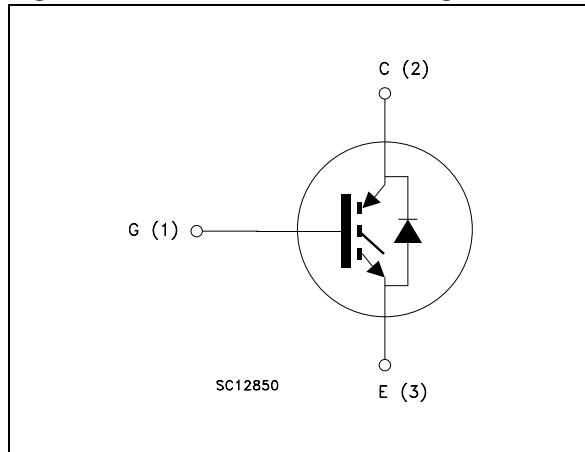
- High frequency inverters
- SMPS and PFC (hard switching too)
- High frequency motor drive

## Description

Thanks to a new lifetime control system, this new PowerMESH™ technology-based series of devices exhibits very low turn-off energy, representing the best trade-off between on-state voltage and switching losses and thus allowing very high operating frequencies.



**Figure 1. Internal schematic diagram**



**Table 1. Device summary**

Order codes	Marking	Package	Packaging
STGBL6NC60DIT4	GBL6NC60DI	D²PAK	Tape and reel
STGDL6NC60DIT4	GDL6NC60DI	DPAK	Tape and reel
STGPL6NC60DI	GPL6NC60DI	TO-220	Tube
STGFL6NC60DI	GFL6NC60DI	TO-220FP	Tube

## Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value			Unit
		DPAK	TO-220 D <sup>2</sup> PAK	TO-220FP	
$V_{CES}$	Collector-emitter voltage ( $V_{GE} = 0$ )	600			V
$I_C^{(1)}$	Collector current (continuous) at $T_C = 25^\circ\text{C}$	13	14	7	A
$I_C^{(1)}$	Collector current (continuous) at $T_C = 100^\circ\text{C}$	5	6	3	A
$I_{CL}^{(2)}$	Turn-off latching current	18			A
$I_{CP}^{(3)}$	Pulsed collector current	18			A
$V_{GE}$	Gate-emitter voltage	$\pm 20$			V
$I_F$	Diode RMS forward current at $T_C = 25^\circ\text{C}$	10			A
$I_{FSM}$	Surge non repetitive forward current $t_p=10\text{ms}$ sinusoidal	25			A
$P_{TOT}$	Total dissipation at $T_C = 25^\circ\text{C}$	50	56	22	W
$V_{ISO}$	Isolation withstand voltage (RMS) from all three leads to external heat sink ( $t=1\text{ s}; T_C=25^\circ\text{C}$ )	--	--	2500	V
$T_j$	Operating junction temperature	–55 to 150			°C

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{j(\max)} - T_C}{R_{thj-c} \times V_{CE(sat)(\max)}(T_{j(\max)}, I_C(T_C))}$$

2.  $V_{clamp} = 80\%$ , ( $V_{CES}$ ),  $T_j = 150^\circ\text{C}$ ,  $R_G = 10\ \Omega$ ,  $V_{GE} = 15\text{ V}$
3. Pulse width limited by maximum junction temperature and turn-off within RBSOA

**Table 3. Thermal data**

Symbol	Parameter	Value			Unit
		DPAK	TO-220 D <sup>2</sup> PAK	TO-220FP	
$R_{thj-case}$	Thermal resistance junction-case IGBT max.	2.5	2.2	5.6	°C/W
	Thermal resistance junction-case diode max.	4.5	4	7	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient max.	100	62.5		°C/W

## 2 Electrical characteristics

( $T_j=25^\circ\text{C}$  unless otherwise specified)

**Table 4. Static electrical characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(\text{BR})\text{CES}}$	Collector-emitter breakdown voltage ( $V_{GE} = 0$ )	$I_C = 1 \text{ mA}$	600			V
$V_{CE(\text{sat})}$	Collector-emitter saturation voltage	$V_{GE} = 15 \text{ V}, I_C = 1.5 \text{ A}$ $V_{GE} = 15 \text{ V}, I_C = 3 \text{ A}$ $V_{GE} = 15 \text{ V}, I_C = 3 \text{ A}, T_j = 125^\circ\text{C}$		1.9 2.2 2	2.9	V V V
$V_{GE(\text{th})}$	Gate threshold voltage	$V_{CE} = V_{GE}, I_C = 250 \mu\text{A}$	3.75		5.75	V
$I_{CES}$	Collector cut-off current ( $V_{GE} = 0$ )	$V_{CE} = 600 \text{ V}$ $V_{CE} = 600 \text{ V}, T_j = 125^\circ\text{C}$			50 5	$\mu\text{A}$ mA
$I_{GES}$	Gate-emitter leakage current ( $V_{CE} = 0$ )	$V_{GE} = \pm 20 \text{ V}$			$\pm 100$	nA
$g_{fs}$	Forward transconductance	$V_{CE} = 15 \text{ V}, I_C = 3 \text{ A}$		3		S

**Table 5. Dynamic electrical characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{ies}$ $C_{oes}$ $C_{res}$	Input capacitance Output capacitance Reverse transfer capacitance	$V_{CE} = 25 \text{ V}, f = 1 \text{ MHz}$ , $V_{GE} = 0$	-	208 32.5 5.4	-	pF pF pF
$Q_g$ $Q_{ge}$ $Q_{gc}$	Total gate charge Gate-emitter charge Gate-collector charge	$V_{CE} = 390 \text{ V}, I_C = 3 \text{ A}$ , $V_{GE} = 15 \text{ V}$ (see Figure 17)	-	12 2.6 4.9	-	nC nC nC

**Table 6. Switching on/off (inductive load)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$ ( $di/dt$ ) <sub>on</sub>	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 390 \text{ V}$ , $I_C = 3 \text{ A}$ $R_G = 10 \Omega$ , $V_{GE} = 15 \text{ V}$ (see Figure 18)	-	6.7 3.7 930	-	ns ns A/ $\mu\text{s}$
$t_{d(on)}$ $t_r$ ( $di/dt$ ) <sub>on</sub>	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 390 \text{ V}$ , $I_C = 3 \text{ A}$ $R_G = 10 \Omega$ , $V_{GE} = 15 \text{ V}$ , $T_j = 125^\circ\text{C}$ (see Figure 18)	-	6.5 4 820	-	ns ns A/ $\mu\text{s}$
$t_r(V_{off})$ $t_d(off)$ $t_f$	Off voltage rise time Turn-off delay time Current fall time	$V_{CC} = 390 \text{ V}$ , $I_C = 3 \text{ A}$ , $R_{GE} = 10 \Omega$ , $V_{GE} = 15 \text{ V}$ (see Figure 18)	-	17 46 47	-	ns ns ns
$t_r(V_{off})$ $t_d(off)$ $t_f$	Off voltage rise time Turn-off delay time Current fall time	$V_{CC} = 390 \text{ V}$ , $I_C = 3 \text{ A}$ , $R_{GE} = 10 \Omega$ , $V_{GE} = 15 \text{ V}$ , $T_j = 125^\circ\text{C}$ (see Figure 18)	-	35 67 55	-	ns ns ns

**Table 7. Switching energy (inductive load)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{on}^{(1)}$ $E_{off}^{(2)}$ $E_{ts}$	Turn-on switching losses Turn-off switching losses Total switching losses	$V_{CC} = 390 \text{ V}$ , $I_C = 3 \text{ A}$ $R_G = 10 \Omega$ , $V_{GE} = 15 \text{ V}$ (see Figure 18)	-	32 24 56	-	$\mu\text{J}$ $\mu\text{J}$ $\mu\text{J}$
$E_{on}^{(1)}$ $E_{off}^{(2)}$ $E_{ts}$	Turn-on switching losses Turn-off switching losses Total switching losses	$V_{CC} = 390 \text{ V}$ , $I_C = 3 \text{ A}$ $R_G = 10 \Omega$ , $V_{GE} = 15 \text{ V}$ , $T_j = 125^\circ\text{C}$ (see Figure 18)	-	51 46 97	-	$\mu\text{J}$ $\mu\text{J}$ $\mu\text{J}$

1. Eon is the turn-on losses when a typical diode is used in the test circuit in (see Figure 19). If the IGBT is offered in a package with a co-pak diode, the co-pak diode is used as external diode. IGBTs and diode are at the same temperature ( $25^\circ\text{C}$  and  $125^\circ\text{C}$ )
2. Turn-off losses include also the tail of the collector current

**Table 8. Collector-emitter diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_F$	Forward on-voltage	$I_F = 1 \text{ A}$ $I_F = 3 \text{ A}$ $I_F = 3 \text{ A}$ , $T_j = 125^\circ\text{C}$	-	1.8 1.3	1.7	V V V
$t_{rr}$ $Q_{rr}$ $I_{rrm}$	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_F = 3 \text{ A}$ , $V_R = 40 \text{ V}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ (see Figure 19)	-	23 21 1.5	-	ns nC A
$t_{rr}$ $Q_{rr}$ $I_{rrm}$	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_F = 3 \text{ A}$ , $V_R = 40 \text{ V}$ , $T_j = 125^\circ\text{C}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ (see Figure 19)	-	47 51 2	-	ns nC A

## 2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

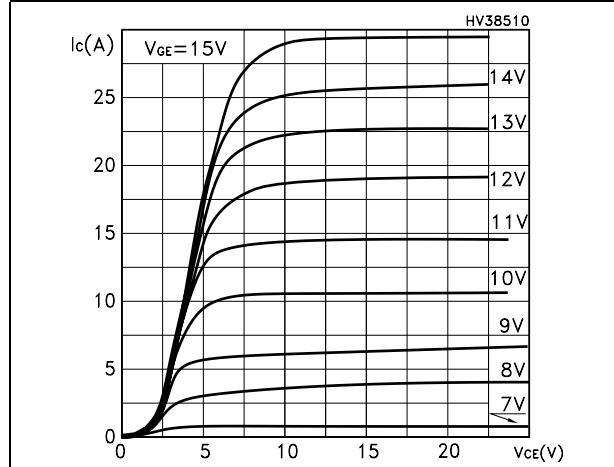


Figure 4. Transconductance

Figure 3. Transfer characteristics

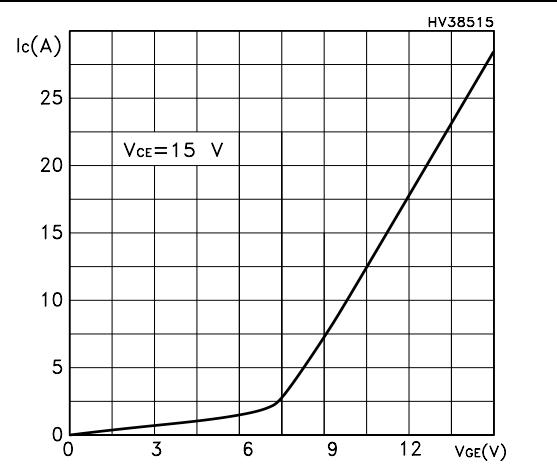


Figure 5. Collector-emitter on voltage vs temperature

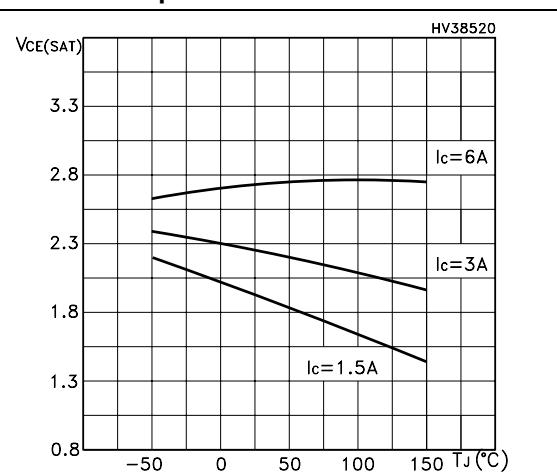
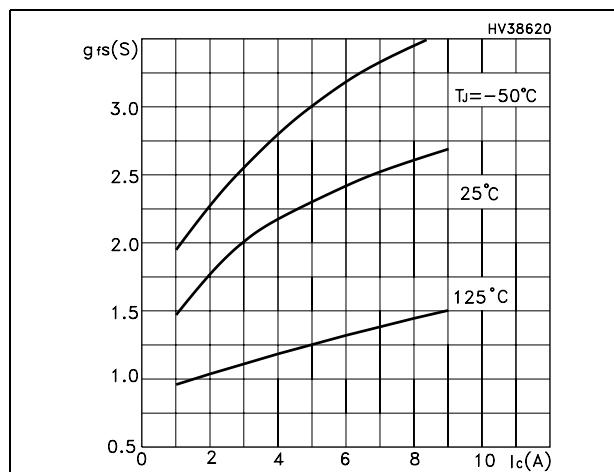
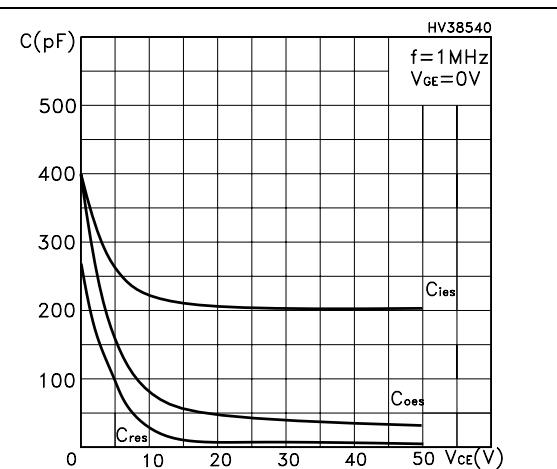
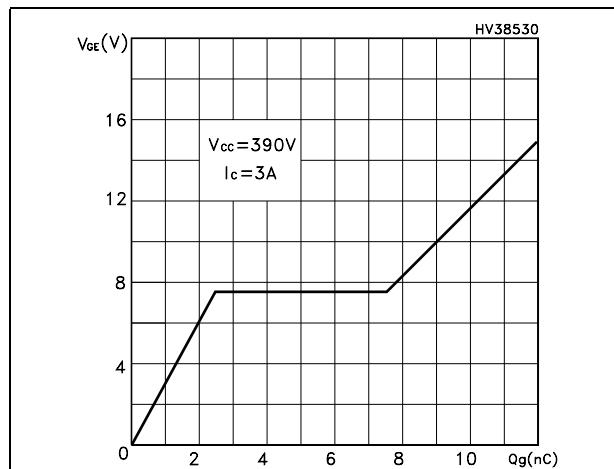
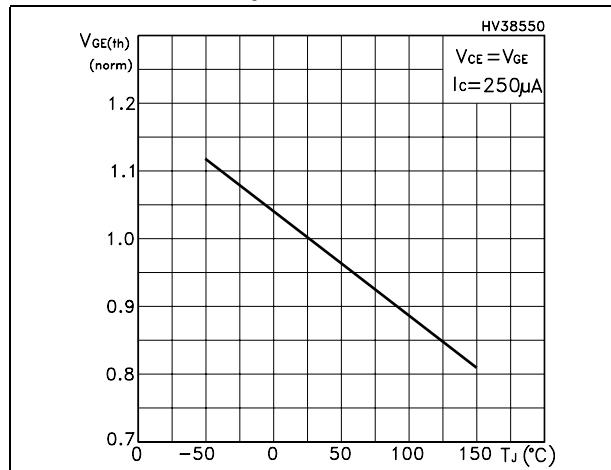
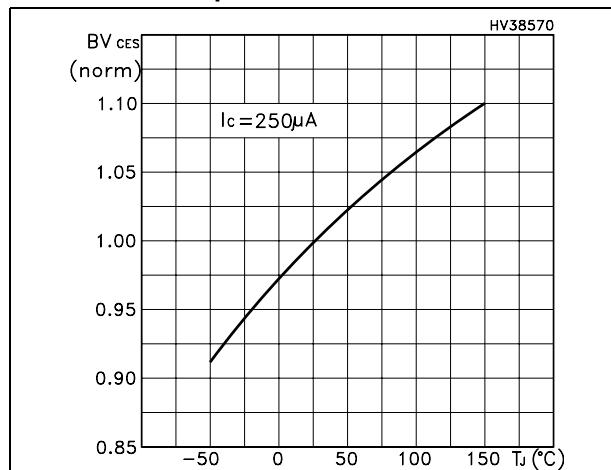
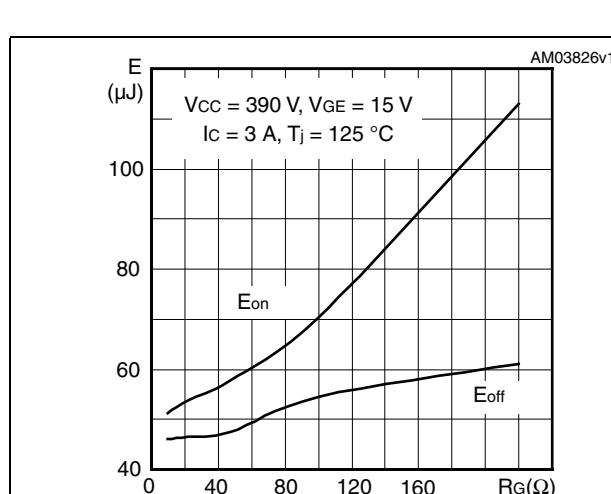
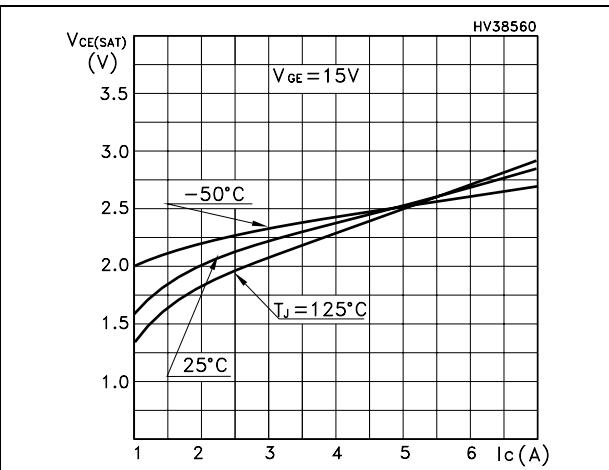
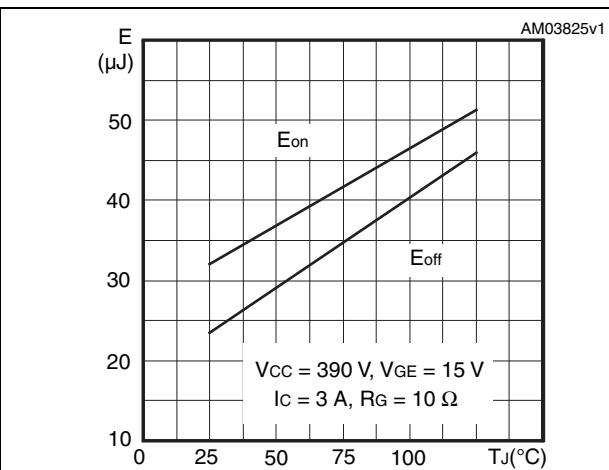
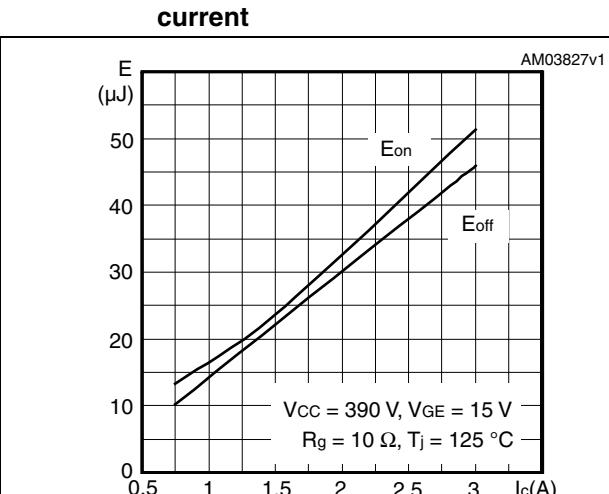
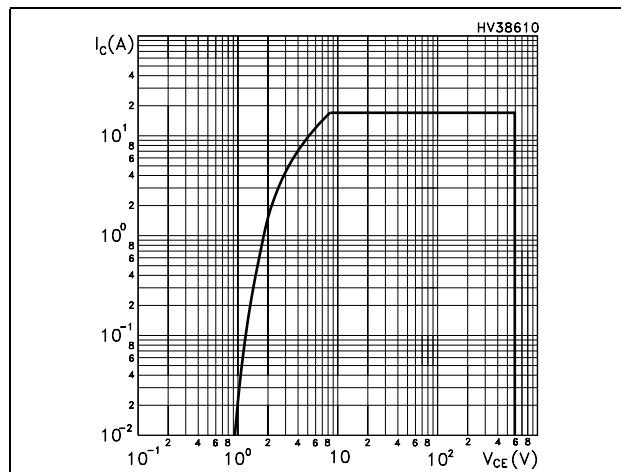
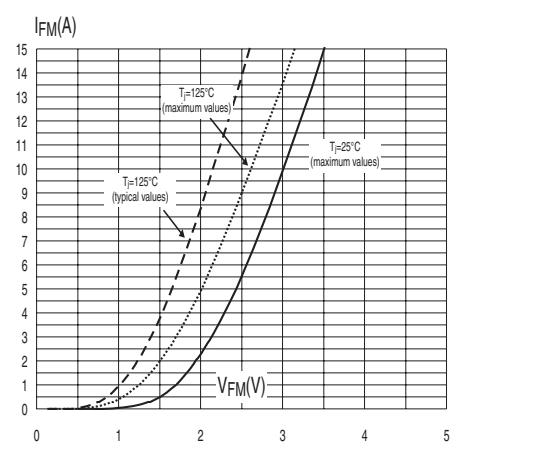


Figure 6. Gate charge vs gate-source voltage    Figure 7. Capacitance variations

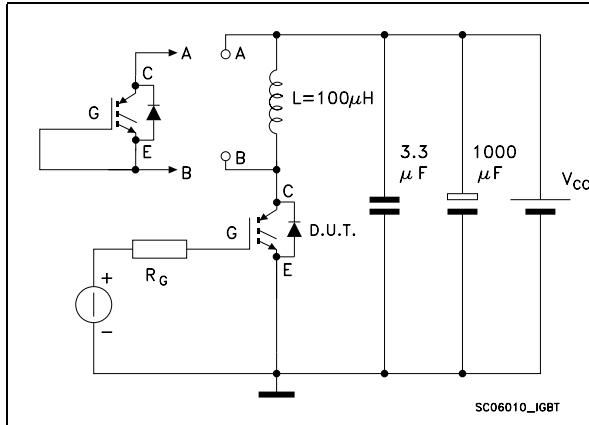


**Figure 8. Normalized gate threshold voltage vs temperature****Figure 10. Normalized breakdown voltage vs temperature****Figure 12. Switching losses vs gate resistance****Figure 9. Collector-emitter on voltage vs collector current****Figure 11. Switching losses vs temperature****Figure 13. Switching losses vs collector current**

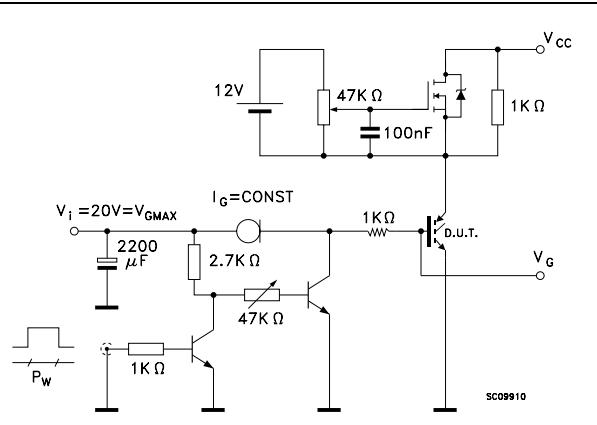
**Figure 14. RBSOA****Figure 15. Forward voltage drop versus forward current**

### 3 Test circuits

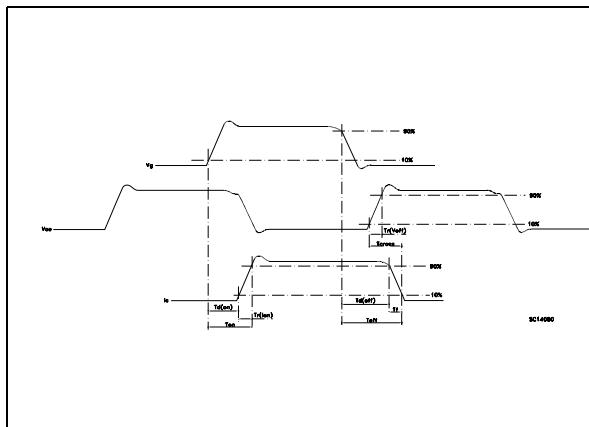
**Figure 16. Test circuit for inductive load switching**



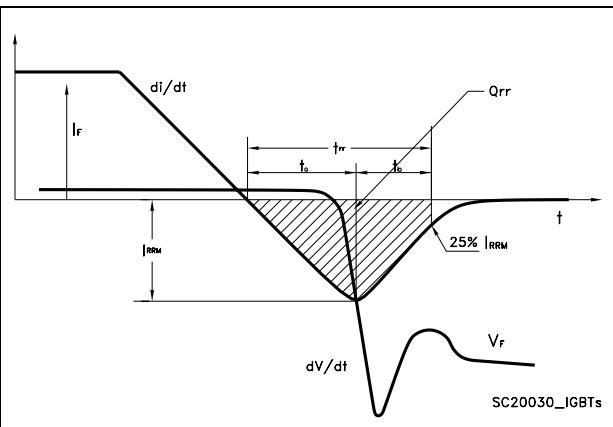
**Figure 17. Gate charge test circuit**



**Figure 18. Switching waveform**



**Figure 19. Diode recovery time waveform**

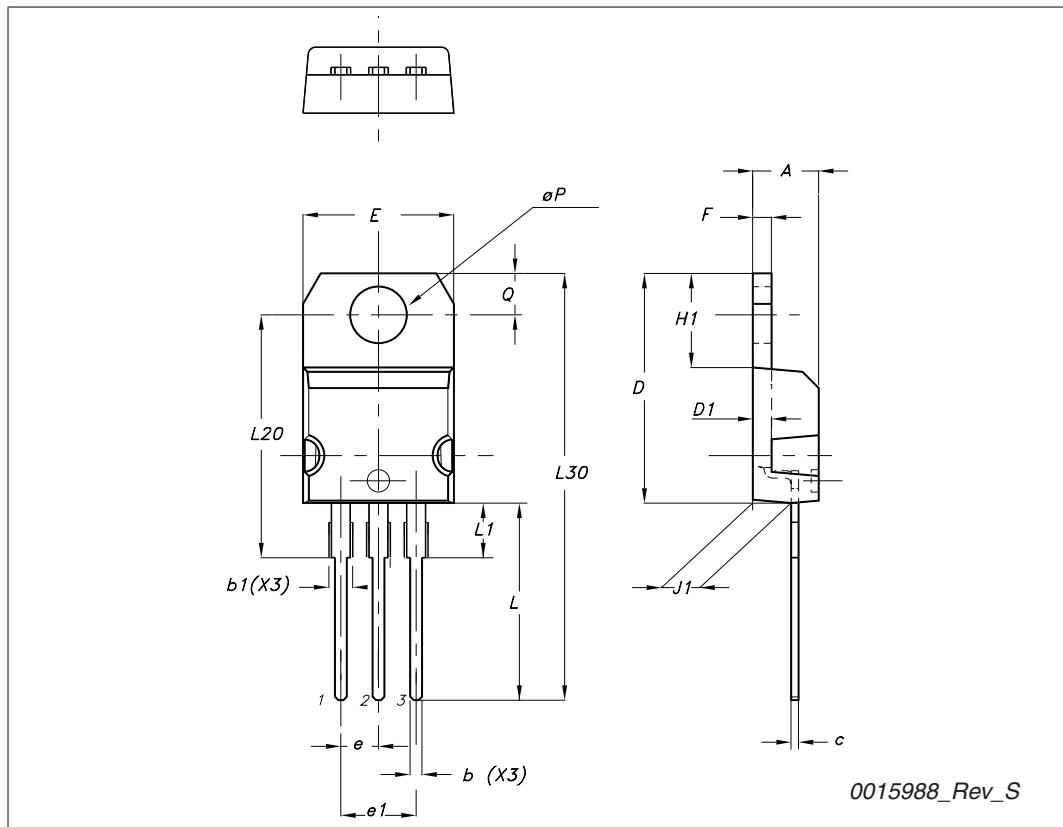


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com).  
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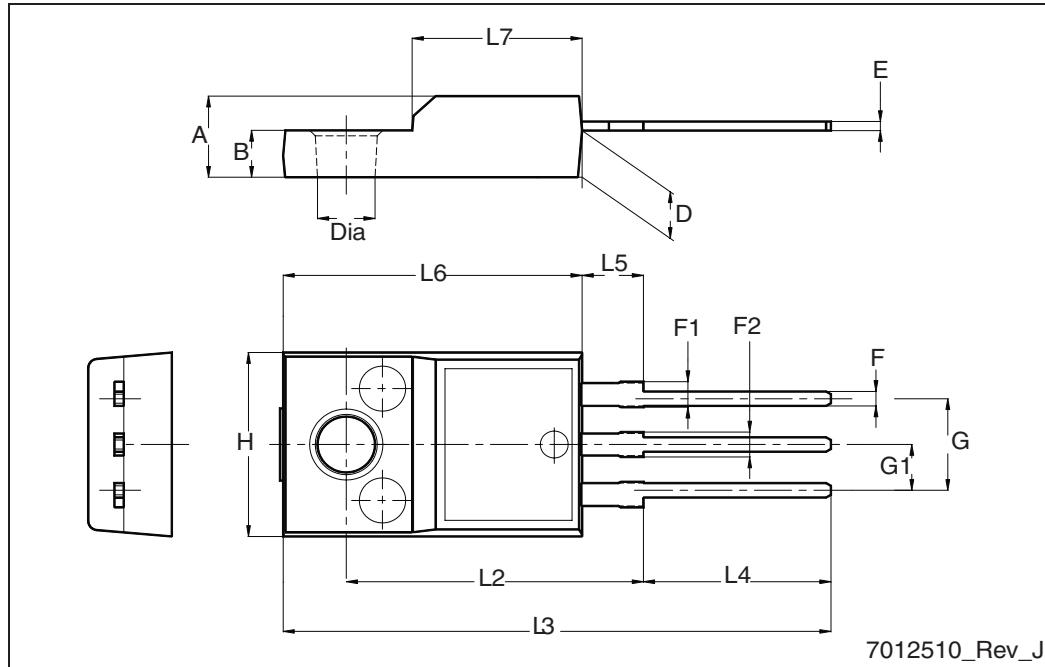
## TO-220 type A mechanical data

Dim	mm		
	Min	Typ	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
$\emptyset P$	3.75		3.85
Q	2.65		2.95



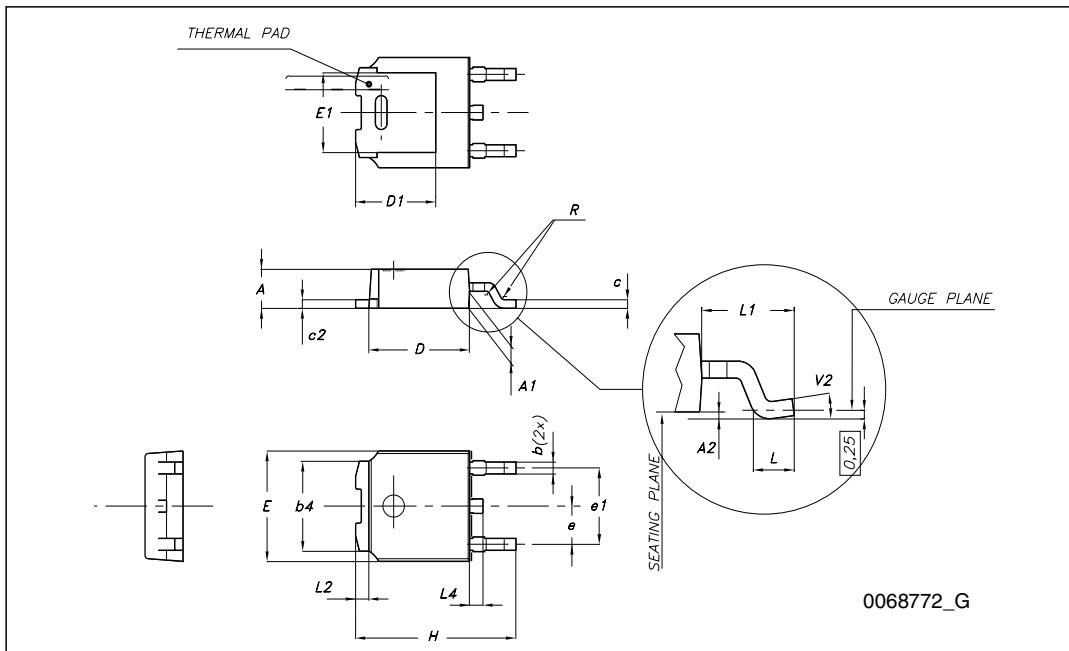
## TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.5
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2



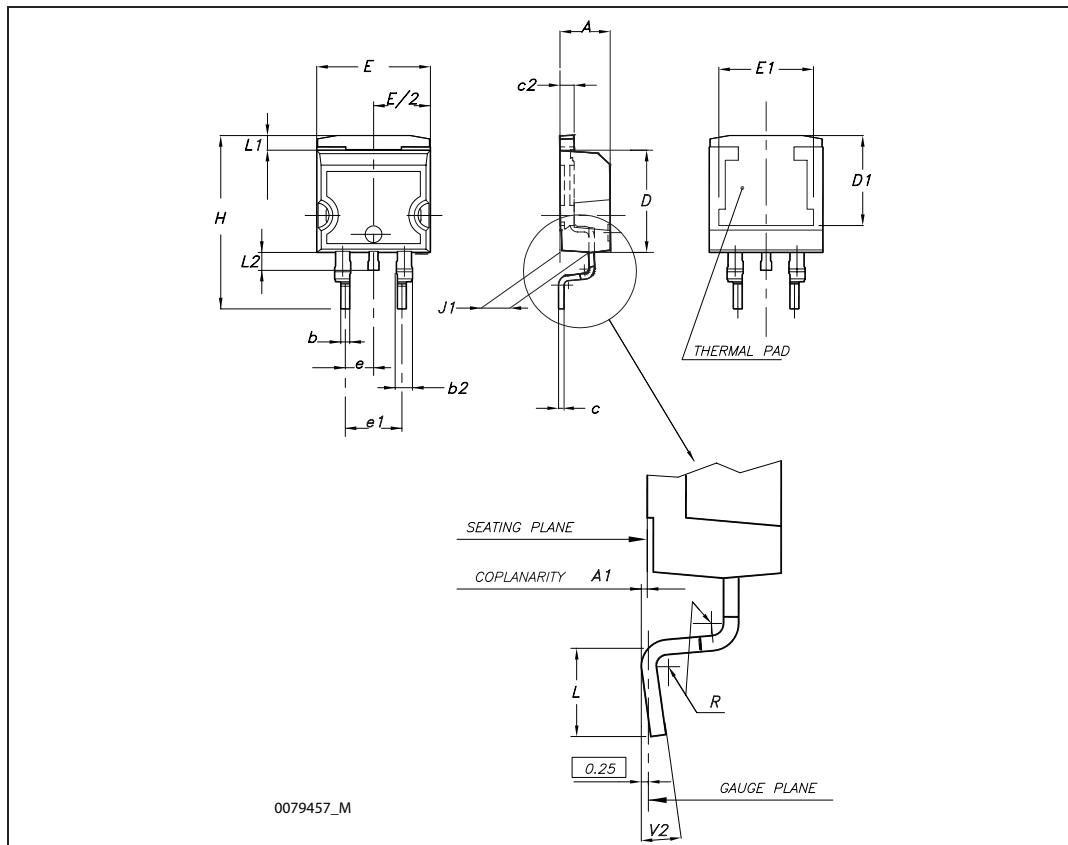
## TO-252 (DPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0 °		8 °



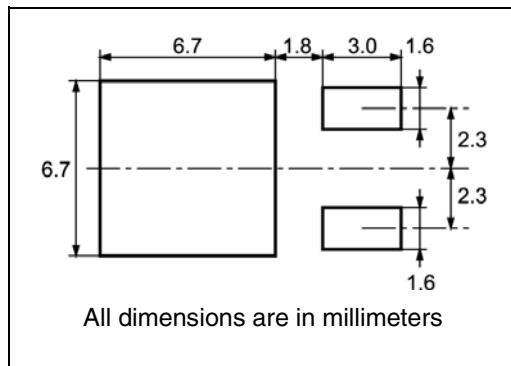
D<sup>2</sup>PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°

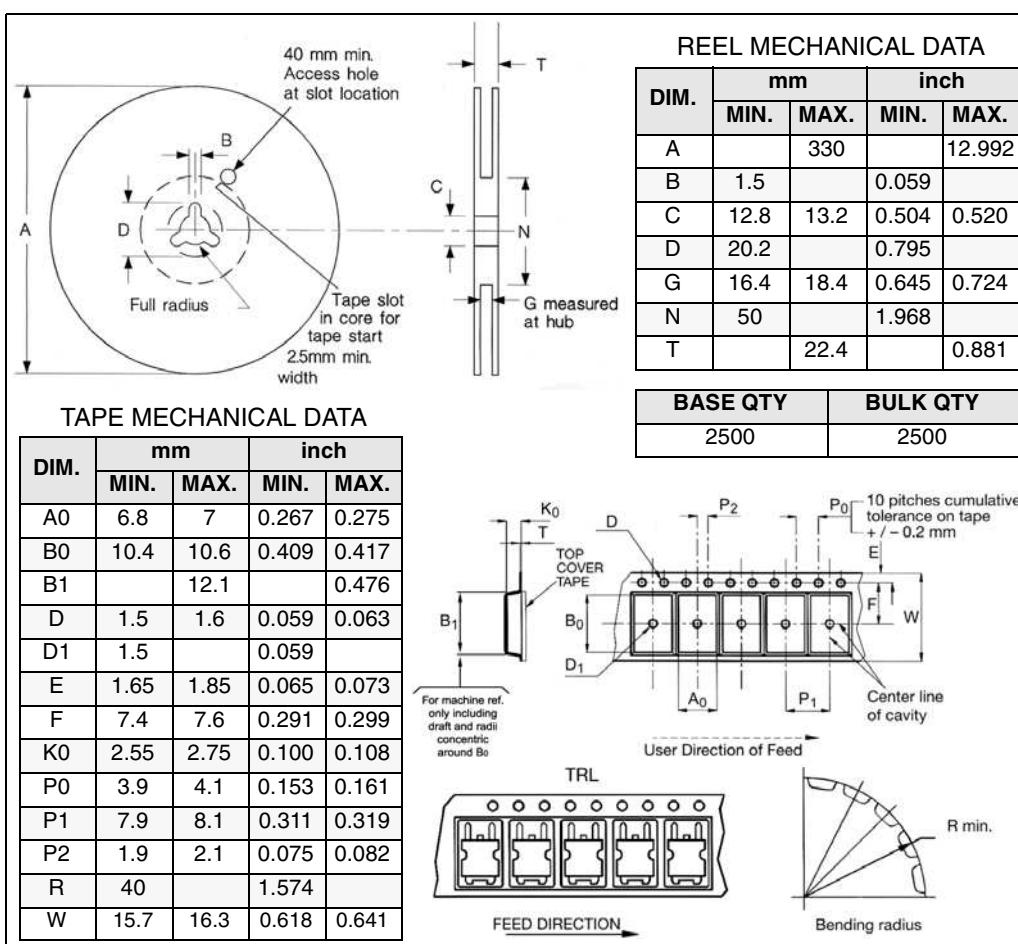


## 5 Packaging mechanical data

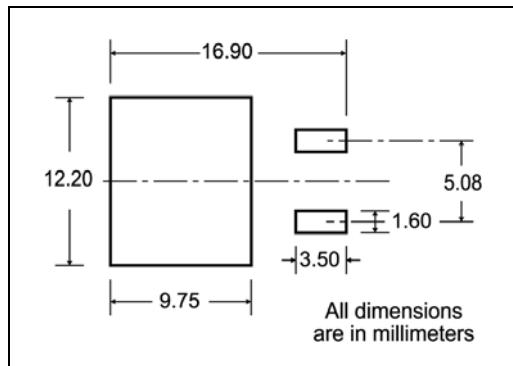
### DPAK FOOTPRINT



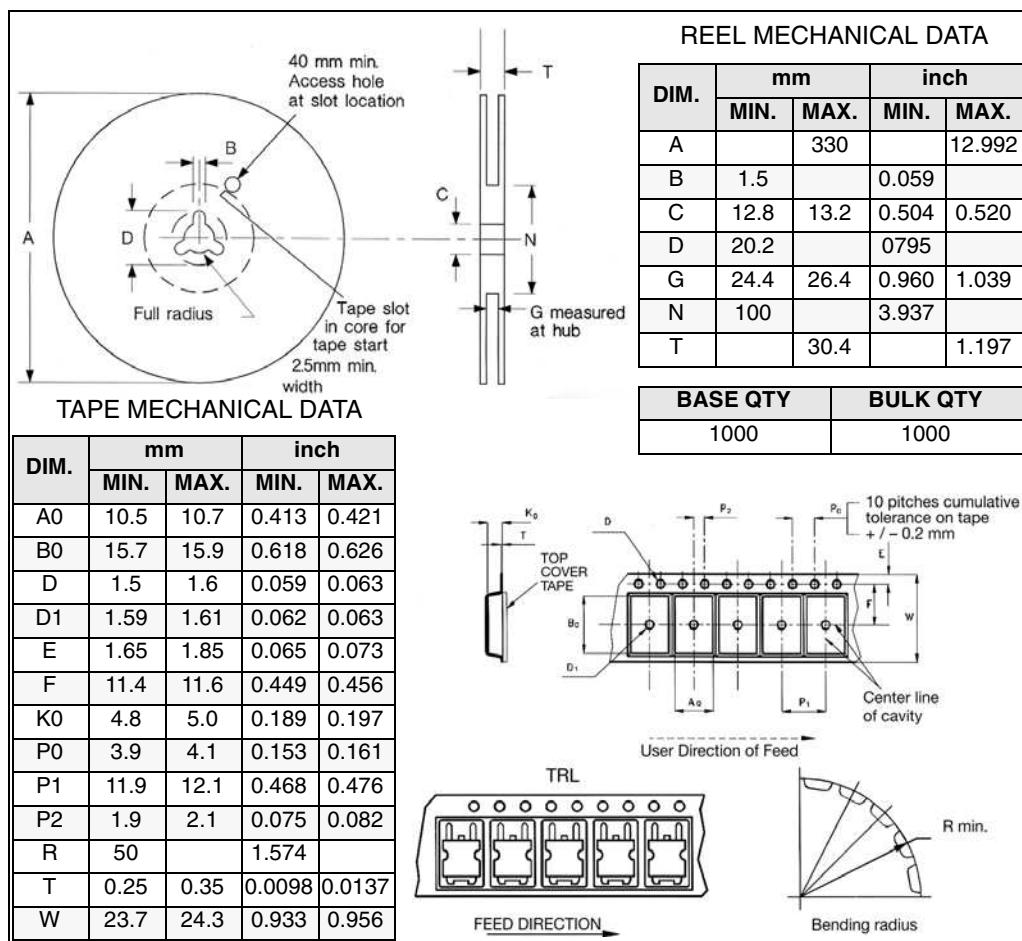
### TAPE AND REEL SHIPMENT



## D<sup>2</sup>PAK FOOTPRINT



## TAPE AND REEL SHIPMENT



## 6 Revision history

**Table 9. Document revision history**

Date	Revision	Changes
27-Mar-2009	1	First release
13-Aug-2009	2	Document status promoted from preliminary data to datasheet, inserted <a href="#">Section 2.1: Electrical characteristics (curves)</a> , updated TO-220 and TO-220FP package mechanical data

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